

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D@25^{\circ}C$
650V	38mΩ@18V	73A

Feature

- Wide bandgap SiC MOSFET technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed switching
- Low reverse recovery(Qrr)

Application

- Switch Mode Power Supplies
- Renewable Energy
- On Board Charger
- High Voltage DC/DC Converters

Package

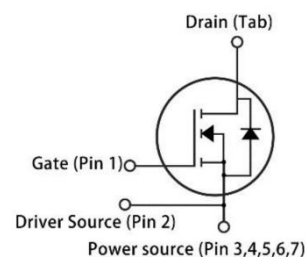


TO-263-7

Marking



Circuit diagram



Absolute maximum ratings ($T_c=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Test Condition	Value	Unit
Drain-Source Voltage	V_{DSmax}	$V_{GS} = 0V, I_D = 100\mu A$	650	V
Gate-Source Voltage	V_{GSmax}	AC ($f > 1 \text{ Hz}$)	-10/+25	V
Gate-Source Voltage	V_{GSOP}	Static	-4/+18	V
Continuous Drain Current	I_D	$V_{GS}=18V, T_C=25^{\circ}C$	73	A
		$V_{GS}=18V, T_C=100^{\circ}C$	52	A
Pulsed Drain Current	$I_{D,pulse}$	Pulse with t_p limited by T_{Jmax}	146	A
Power Dissipation	P_D	$T_J=175^{\circ}C$	181	W
Thermal Resistance (Typ)	$R_{\theta JC}$	Junction-to-Case	0.83	$^{\circ}C/W$
Junction Temperature	T_J		-55 ~ +175	$^{\circ}C$
Storage Temperature	T_{STG}		-55 ~ +175	$^{\circ}C$

Electrical characteristics (T_j=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =100μA	650			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =650V,V _{GS} = 0V			50	μA
Gate-Source leakage current	I _{GSS}	V _{GS} =18V, V _{DS} = 0V			250	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =16mA		3.0		V
		V _{DS} =V _{GS} , I _D =16mA ,T _J =175℃		2.0		
Drain-source on-resistance	R _{DS(on)}	V _{GS} =18V, I _D =40A		26	38	mΩ
		V _{GS} =18V, I _D =40A,T _j = 175℃		35		
Transconductance	g _{fs}	V _{DS} =18V, I _D =40A		27		S
		V _{DS} =18V, I _D =40A,T _j = 175℃		25		
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =600V,V _{GS} =0V,f =1MHz V _{AC} =25mV		2543		pF
Output Capacitance	C _{oss}			173		
Reverse Transfer Capacitance	C _{rss}			8		
Total Gate Charge	Q _g	V _{DS} =400V,V _{GS} =-4V/18V, I _D =40A		74.5		nC
Gate-Source Charge	Q _{gs}			29		
Gate-Drain Charge	Q _{gd}			35		
Turn-on delay time	t _{d(on)}	V _{DS} =400V,V _{GS} =-4/+18V, I _D =40A,R _{G(ext)} =5Ω, L = 294μH		2		nS
Turn-on rise time	t _r			18		
Turn-off delay time	t _{d(off)}			18		
Turn-off fall time	t _f			5		
Turn-On Energy	E _{on}			58		μJ
Turn-Off Energy	E _{off}			72		
Total switching energy	E _{tot}			130		
Internal Gate Resistance	R _{G(int)}	f=1 MHz, V _{AC} = 25mV		1.2		Ω
Source-Drain Diode characteristics						
Diode Forward Current	I _S	V _{GS} =-4V,T _C =25℃		42		A
Diode Forward voltage	V _{SD}	V _{GS} =-4V, I _{SD} =20A		4.3		V
		V _{GS} =-4V, I _{SD} =20A,T _j =175℃		3.7		
Diode pulse Current	I _{S,pulse}	V _{GS} =-4V, pulse width t _p limited by T _{jmax}		146		A
Reverse Recovery Time	t _{rr}	V _{GS} =-4V,I _{SD} =40A,V _R =400V dif/dt = 3800 A/μs		15		nS
Reverse Recovery Charge	Q _{rr}			348		nC
Peak Reverse Recovery Current	I _{rrm}			25		A

Typical Characteristics

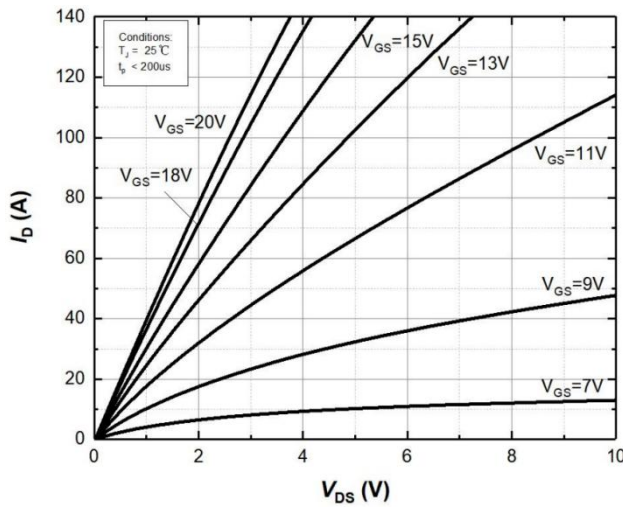


Figure 1. Output characteristics at $T_j=25^\circ\text{C}$

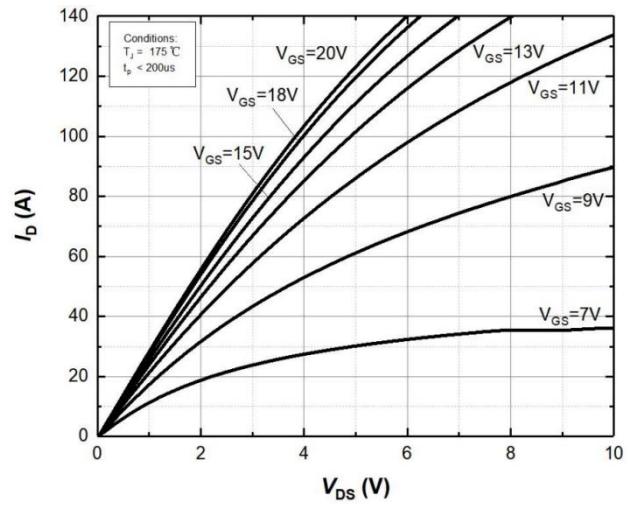


Figure 2. Output characteristics at $T_j=175^\circ\text{C}$

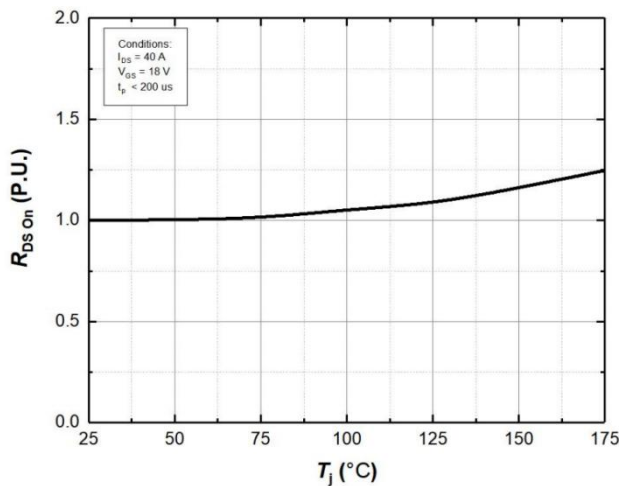


Figure 3. Normalized On-Resistance vs. Temperature

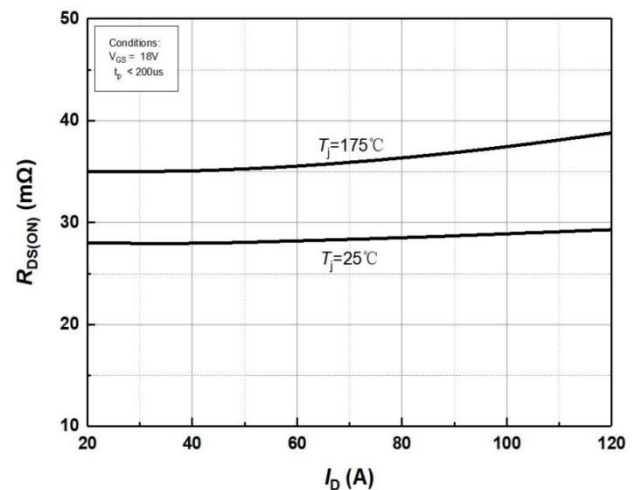


Figure 4. On-Resistance vs. Drain current for Various Temperature

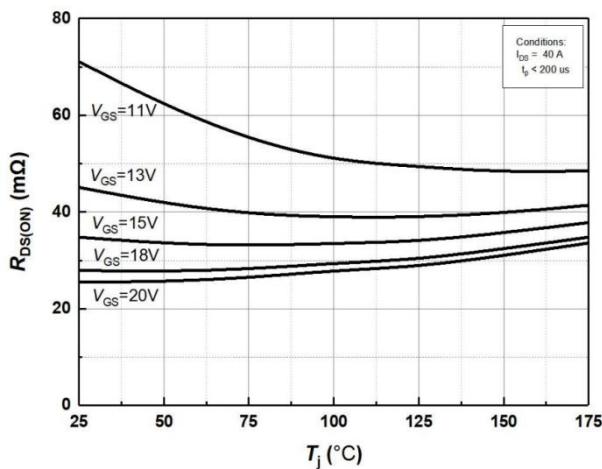


Figure 5. On-Resistance vs. Temperature for Various Gate Voltage

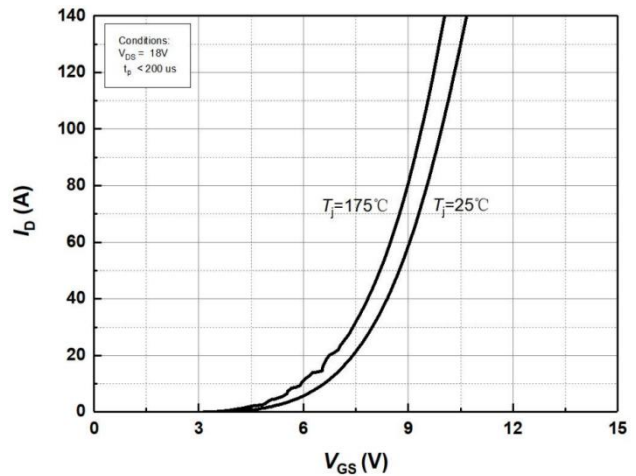


Figure 6. Transfer Characteristics for Various Junction Temperatures

Typical Characteristics

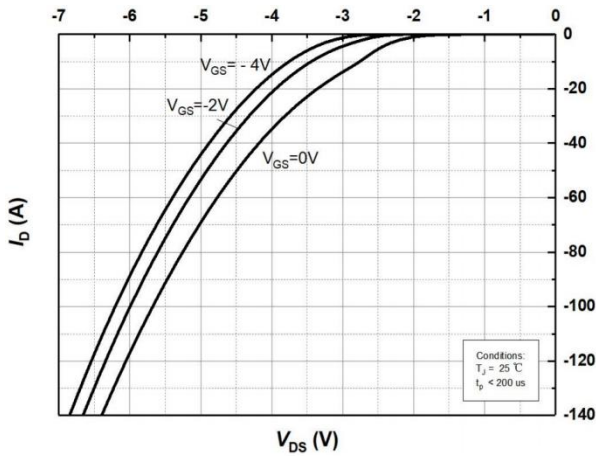


Figure 7. Body Diode Characteristics at $T_j=25^{\circ}\text{C}$

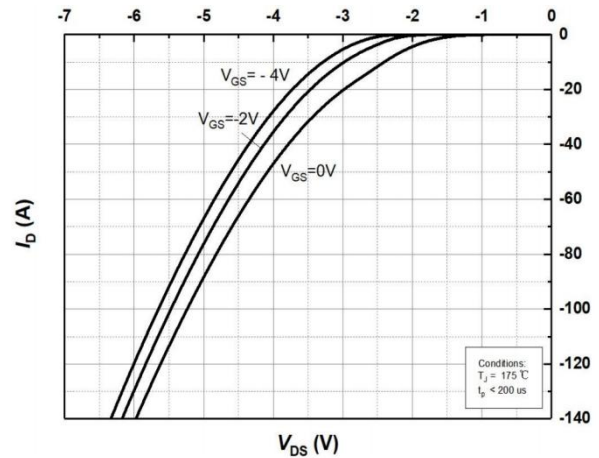


Figure 8. Body Diode Characteristics at $T_j=175^{\circ}\text{C}$

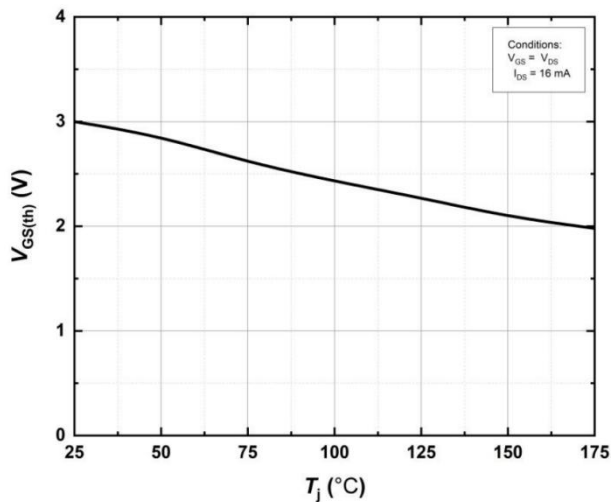


Figure 9. Threshold Voltage vs. Temperature

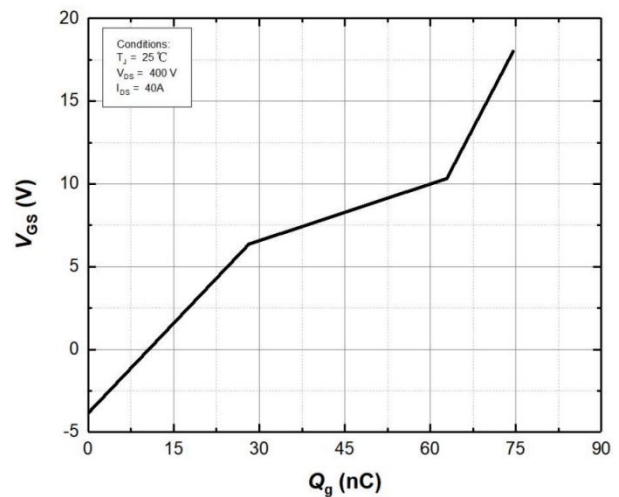


Figure 10. Gate Charge Characteristics

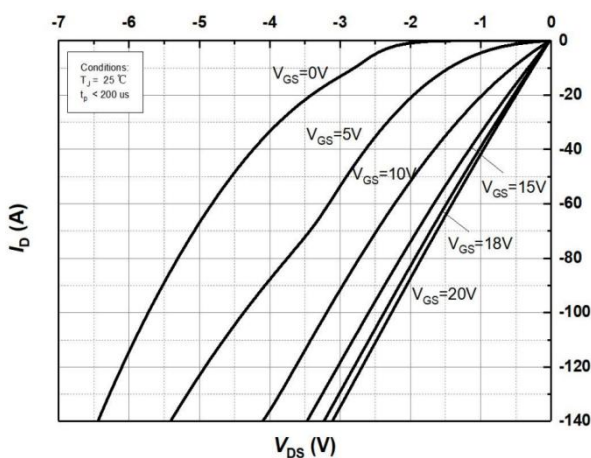


Figure 11. 3rd Quadrant Characteristic at $T_j=25^{\circ}\text{C}$

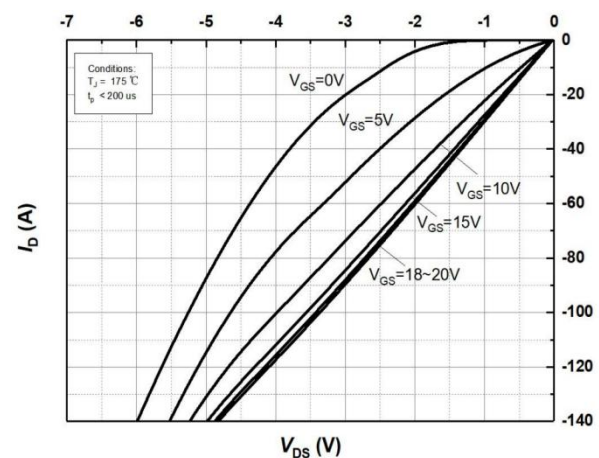


Figure 12. 3rd Quadrant Characteristic at $T_j=175^{\circ}\text{C}$

Typical Characteristics

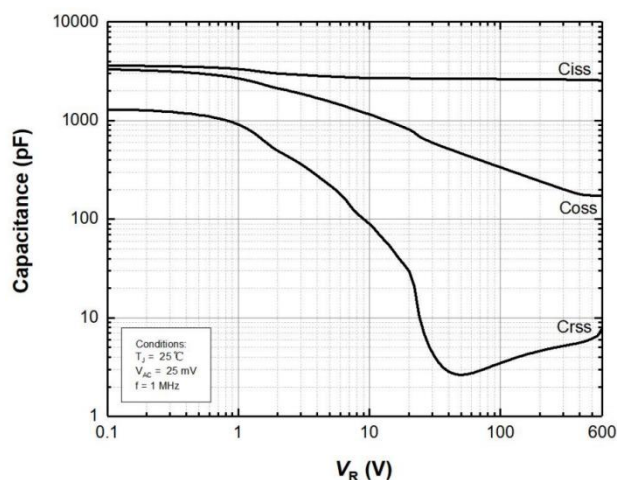


Figure 13. Capacitances vs. Drain-Source Voltage (0 - 600V)

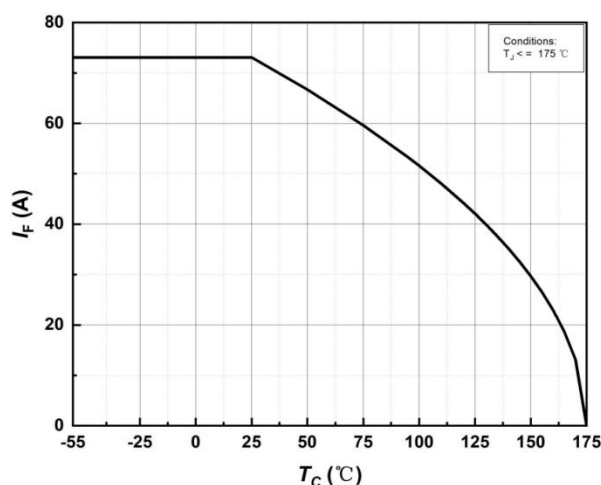


Figure 14. Continuous Drain Current Derating vs Case Temperature

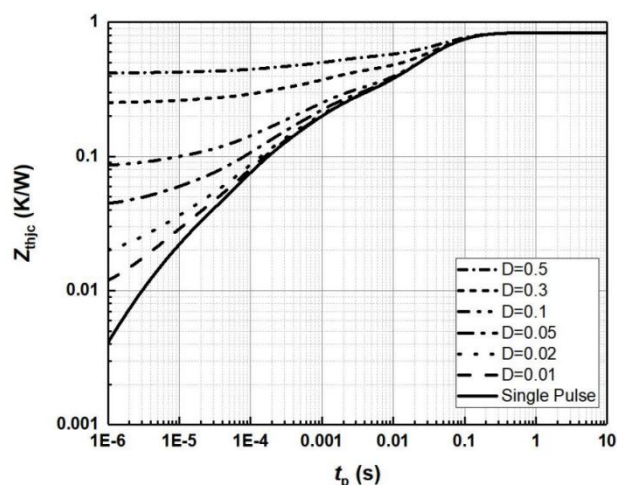


Figure 15. Transient Thermal Impedance (Junction - Case)

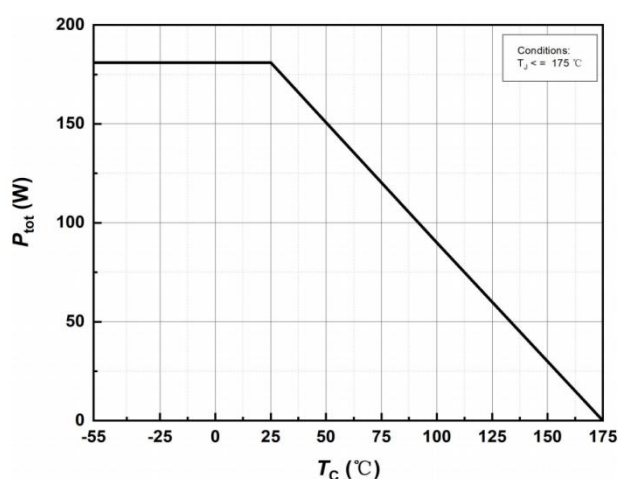


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

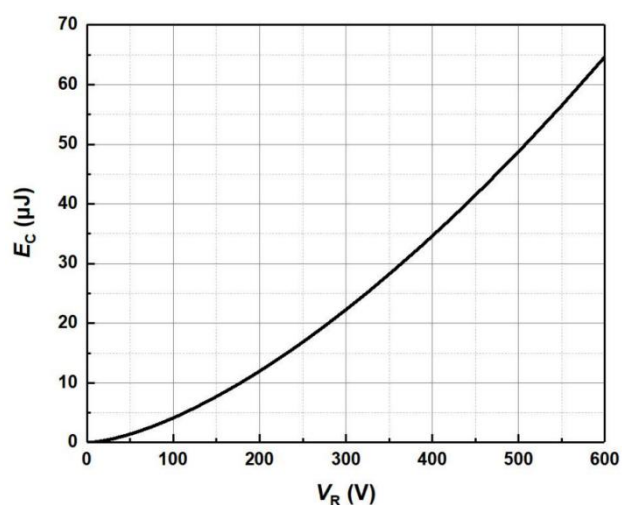


Figure 17. Output Capacitor Stored Energy

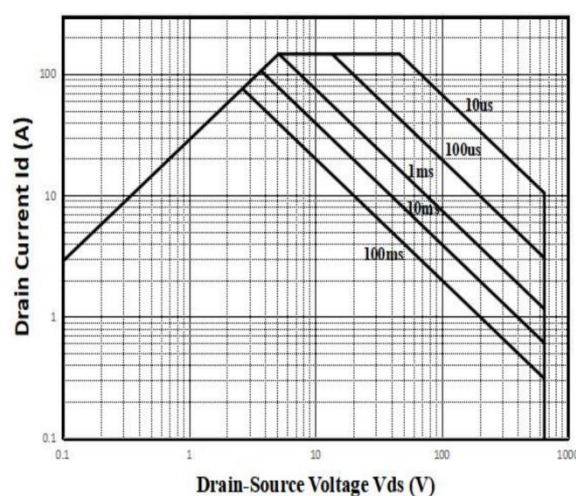


Figure 18. Safe Operating Area

Typical Characteristics

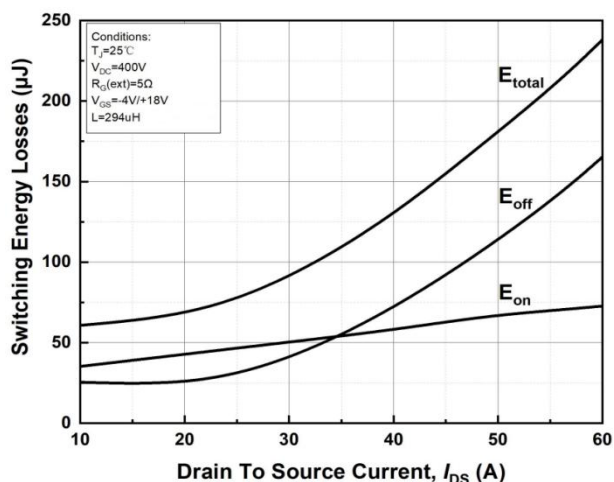


Figure 19. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 400\text{V}$)

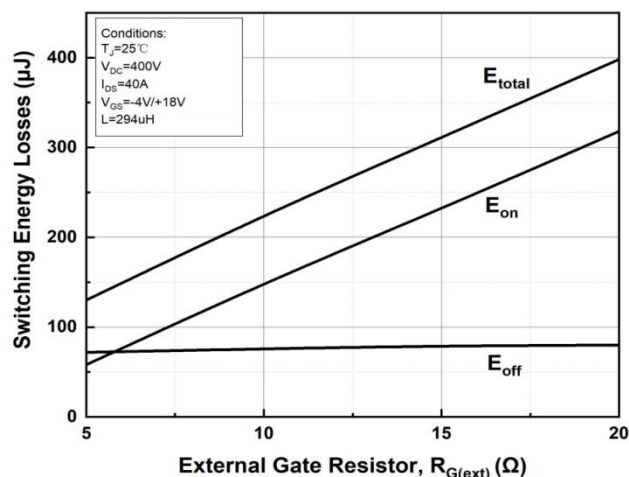


Figure 20. Clamped Inductive Switching Energy vs. $R_{G(\text{ext})}$

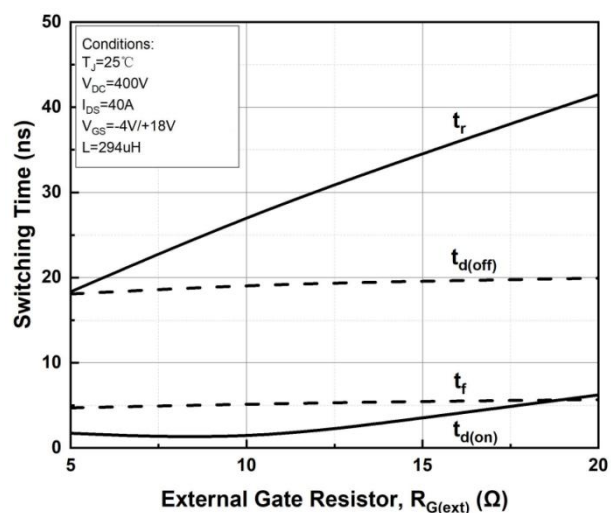
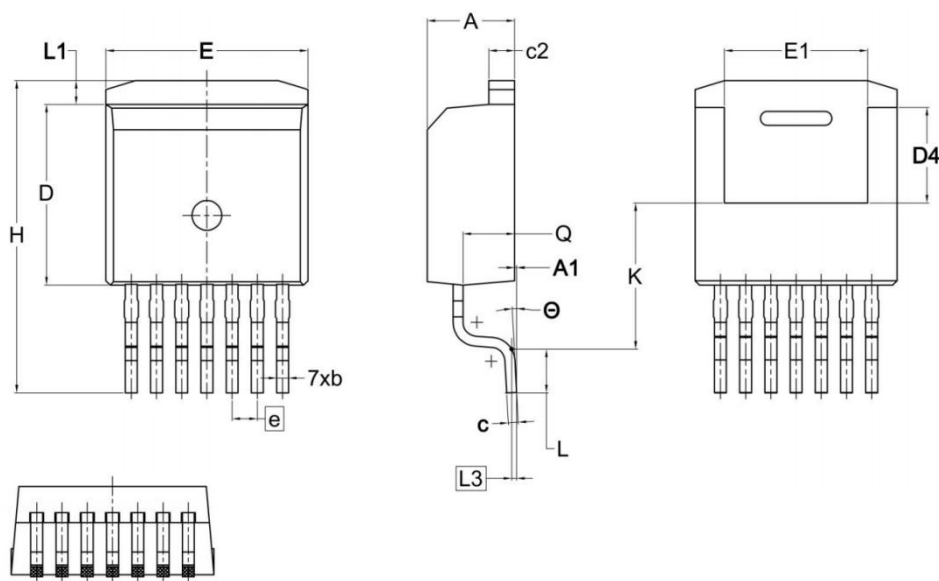


Figure 21. Switching Times vs. $R_{G(\text{ext})}$

TO-263-7 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.500	0.169	0.177
A1	0.000	0.250	0.000	0.010
b	0.500	0.700	0.020	0.028
c	0.450	0.600	0.018	0.024
c2	1.200	1.400	0.047	0.055
D	8.930	9.230	0.352	0.363
D4	4.650	4.950	0.183	0.195
E	10.080	10.280	0.397	0.405
E1	6.820	7.620	0.269	0.300
e	1.270 BSC.		0.050 BSC.	
H	15.000	16.000	0.591	0.630
K	7.300 BSC.		0.287 BSC.	
L	1.900	2.500	0.075	0.098
L1	1.000	1.400	0.039	0.055
L3	0.250 BSC.		0.010 BSC.	
Q	2.450	2.750	0.096	0.108
θ	0°	7°	0°	7°